



THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Jack H. Yuan et al.

Title: Non-Volatile Memory Cell Array Having Discontinuous Source and Drain Diffusions Contacted By Continuous Bit Line Conductors and Methods of Forming

Application No.: 10/822,966 Filing Date: April 12, 2004

Examiner: Le, Thao P. Group Art Unit: 2818

Docket No.: SNDK.217US2 Conf. No.: 3615

Mail Stop RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

AMENDMENT

Sir:

Please amend the application as follows:

Claim Amendments are reflected in the listing of claims, which begins on page 2 of this paper.

Remarks begin on page 4 of this paper.

Attorney Docket No.: SNDK.217US2
Express Mail No.: EV437669050US

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